

5DS32B

Switching Diode



Features

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- High Voltage General Purpose Diode

Item	Characteristics
Wafer size	5inch
Chip size	380*380um

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	VRSM	250	V
Repetitive Peak Reverse Voltage	VRRM	250	V
Average Rectified Forward Current	IF (AV)	200	mA
Repetitive Peak Forward Current	IFRM	625	mA
Non-Repetitive Peak Forward Current @t=1us	IFSM	9	A
Power Dissipation	PD	400	mW
Junction Temperature	Tj	175	degC
Storage Temperature	Tstg	-65to+175	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Breakdown Voltage	BV	250		V	IR=100uA
Forward Voltage	VF		1.0	V	IF=100mA
			1.25	V	IF=200mA
Reverse Current	IR		100	nA	VR=200V
Junction Capacitance	CT		5	pF	VR=0V, f=1MHz
Reverse Recovery Time	trr		50	nsec	IF=IR=30mA RL=100Ω

Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
BV	260		V	IR=100uA
VF1		980	mV	IF=100mA
VF2		1.2	V	IF=200mA
IR		98	nA	VR=200V
CT		5	pF	VR=0V,f=1MHz
trr		50	nsec	IF=IR=30mA,RL=100Ω

Note

Equivalent type : BAV21

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